# Transm ission and SpectralA spects of $T$ ight $B$ inding  

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#### Abstract

1-D system s w ith determ inistic disorder, such as those w ith quasiperiodic or substitution sequence potentialdistributions, have been $m$ uch studied. It w as recently shown that a generalization of quantum Turing $m$ achines (Q TM s), in which potentials are associated w ith elem entary steps or transitions of the com putation, generates potential distributions along com putation paths of states in som e basis B, that are com putable and are thus periodic or have determ inistic disorder. These generalized machines (GQTM s) can be used to investigate the e ect of potentials in causing re ections and reducing the com pletion probability of com putations. This paper expands on this work by determ in ing the spectral and transm ission properties of an exam ple GQTM, which enum erates the integers in succession as binary strings. A potential is associated w ith just one type of step. For $m$ any com putation paths the potential distributions are in itial segm ents of a distribution that is quasiperiodic and corresponds to a substitution sequence. T hus the $m$ ethods developed in the study of $1-\mathrm{D}$ system s can be used to calculate the energy band spectra and Landauer R esistance (LR ). For energies below the barrier height, The LR uctuates rapidly w ith m om entum w ith m in m a close to or at band-gap edges. A lso for several values of the param eters involved there is good transm ission over som emom entum regions.


72.10.-d,89.70.+ c,63.90.+ t

The discovery ofquasicrystals [1], (See [0]3] for recent review s) has stim ulated m uch study of system $\mathrm{s} w$ th determ inistic disorder [4]. These system $s$ are neither random nor periodic. A s part of this work there has been $m$ uch interest in the study, either $w$ ith $K$ ronig-Penney or tight binding $H$ am iltonians, of the spectra and transm ission properties of 1-D system S whose potential distributions correspond to substitution sequences. (T hese are de ned in
 sequences, the spectra are singular continuous and are C antor sets. For the R udin-Shapiro sequence, the spectral properties are unknown [G]. P otential distributions corresponding to circle sequences 10] and the prim e num ber distribution [11] have also been studied.

Transm ission properties of $1-D$ structures for which the potentialdistributions are intial segm ents of substitution sequences have also been studied 12; [16]. O f special interest here are studies of the Landauer Resistance [17,18] for various potential distributions and its relation to the band structure of in nite periodic system swhose unit cells are initialsegm ents of substitution sequences 19, 21].

O ne dim ensional structures of these types also appear in a generalization of quantum Turing $m$ achines introduced elsew here 22]. The generalization consists of $m$ odifying the H am iltonian description of quantum Turing machines ( Q M s) so that potentials are associated $w$ ith som e types of steps or transitions of the com putation as it $m$ oves along paths of states in a suitable basis. The resulting distributions of potentials along these com putation paths are computable and are thus either periodic or determ inistically disordered. As a result generalized quantum Turing machines ( GQTM s) are both quantum com puters and $1-D$ structures of the type of $u$ uch recent interest.

The presence of these potentials m eans that GQ TM s also serve as a test bed to exam ine thee ect ofthese potentials on the transm ission and re ection ofthe com putation state along any com putation path and the com pletion probability for the com putation. The im portance of this for quantum com putation has been repeatedly em phasized by Landauer [23]. He has noted that these potentials, which $m$ ay result from environm ental in uences and errors in construction of actual physicalm odels of the com putation process 24,25], cause re ections back along the com putation path and $m$ ay result in exponential decay or localization of the transm itted state.

This em phasis is based on the fact that in $m u c h$ of the work done so far on quantum com putation, the com putation as been assum ed to proceed sm oothly along com putation paths w ith no potentials present. This is the case whether quantum com puters are used as com puters 26[33] or as sim ulators of other quantum system s 34, 35]. W ork on Shor's quantum algorithm 36] and on quantum gates and quantum error correction 37,38] is also included.

Them ain purpose ofthisw ork is the exam ination ofthee ect ofpotentials on the spectral and transm ission properties of com putation states along com putation paths. The m ethod w illbe based on other work 22] in which potentials are associated w ith som e types of steps or transitions of the com putation as it evolves along paths of states in a suitable basis. The Feynm an H am ittonians for these G Q TM s can, under certain conditions, be decom posed into a direct sum of tight binding $H$ am iltonians, $H={ }^{P}{ }_{i} H_{i}$, where the isum is over com putation paths of states in a basis. The potential distribution, $V_{i}$, in $H_{i}$ depends on the path $i$.

H ere the exam ple GQ TM , which was introduced in other work 22], w ill.be exam ined in detail. This exam ple, the counting GQTM, which enum erates the integers in succession as binary strings, has a potential associated w ith read-1 steps only. (read-1 steps are de ned at the end of Section \#.) For $m$ any paths the potential distribution was seen to be quasicrystalline and to correspond to initialsegm ents of a substitution sequence generated from an in nite alphabet.

B oth the spectral and transm ission properties of the tight binding H am iltonians associated with the counting GQTM will be determ ined. The energy band spectra will be calculated for associated periodic system s. These are 1-D crystals whose unit cells are ( nite sections of) com putation paths that contain the potential distributions being studied. Transm ission properties w ill.be calculated by determ ining the Landauer R esistance of com putation paths for the counting GQ TM. This paper should be read in conjunction w ith [22] as much of the earlier w ork $w$ ill not be repeated.

In the next section the physicalm odel for Q TM s (generalized or not) willbe presented. This will be followed in Section by a brief description of the generalization of QTM s and the decom position of H am iltonians for GQTM s into a sum over paths of tight binding H am iltonians. Com putation paths will be de ned. The counting GQTM will be described in Section $\mathbb{I V}$. The discussion of the step operator and potential distribution w ill be brief as $m$ uch of the $m$ aterial is already given elsew here [22]. The transfer $m$ atrix $w$ illibe de ned for potential distributions containing the rst $2^{N}{ }^{1}$ potentials $w$ ith $N$ an arbitrary positive integer.

The em phasis of Sections $V$ and $V$ is on the spectral gaps and band widths for the associated periodic system s and Landauer R esistance of system s described by tight binding H am iltoniansw ith $2^{N}{ }^{1}$ potentials for the counting G Q TM.Thew idth and separation of the potentials is related to an initial segm ent of a generalized substitution sequence described elsew here 22,39]. The work is exploratory w th em phasis on calculations to show the dependence of these properties on various param eters. A lso as was done by R oy and K han [20], the relation between the Landauer R esistance of a system and the band spectra of the associated periodic system will be investigated.

It should be noted that the only e ect of this generalization is the introduction of potentials along com putation paths. There is no change in the class of Q TM s or in the concept of quantum com putability.

## II. THE PHYSICALMODEL

The physicalm odel for one-tape quantum Turing $m$ achines consists of a two-way in nite one dim ensional lattioe of system $s$ each of which can assum e states in a nite dim ensional H ilbert space. If the space is two dim ensional, the system s are referred to as qubits. This term willbe used here even if the dim ensionality is greater than two. It is often convenient but not necessary to consider the lattice as spin system s , e.g. spin $1 / 2$ system s for binary qubits.

A head which can assume any one of a nite number of orthogonal states jit with l m oves along the lattice interacting $w$ ith qubits at or next to its location on the lattioe. Elem entary Q TM actions include one or more of (1) head $m$ otion one lattioe site to the
right or left, (2) change of the state of the qubit scanned or read by the head, (3) change of the head state. W hat happens depends on the states of the head and scanned qubit.

H ere the system states are all assum ed to lie in a separable H ilbert space H. B ased on the above description a particular basis, the com putation basis, de ned by the set of states fj ; j; S ig and which spans $H$, is used. H ere $l ; j$ refer to the intemal state and lattioe position of the head. The qubit lattice com putation basis state $\mathrm{j}^{\mathrm{S}} \mathrm{i}={ }_{\mathrm{m}}^{\mathrm{m}}=1 \mathrm{j}(\mathrm{m}) \mathrm{i}$ where S is a function from the integers to the qubit state labels (e.g. f0; 1 g ) such that $S(m) \notin 0$ for at $m$ ost a nite number of values of $m$. This condition, the 0 tail state condition, is one of $m$ any that can be im posed to keep the basis denum erable. N ote that all qubit states, such as ajoi + bjli for arbitrary a;b and sum s of products of these states are included as appropriate linear superpositions of the com putation basis states.

## III. TIGHTBIND $\mathbb{I N G}$ HAM ILTON IANSFROM QUANTUM TURING MACHINES

O ne begins by associating a bounded linear operator $T$ w th each GQTM.T is referred to as a step operator for the G Q TM because iteration of T (or its adjoint) corresponds to the successive steps in the forw ard (or badkward) tim e direction of the GQ TM.An in nitesim al tim e interval is associated w ith the steps of $T$ so that it can be used directly to construct a tim e independent H am iltonian. T he speci c construction used here is that proposed by Feynm an 40]:

$$
H=K\left(\begin{array}{lll}
(2 & T & T^{Y} \tag{1}
\end{array}\right)
$$

where K is a constant. This de nition has the advantage that if $\mathrm{T}=\mathrm{Y}$ where Y is the bilateral shift along the lattioe, then $H$ is the kinetic energy of free head m otion on the lattioe. A s such it is equivalent to the sym $m$ etrized discrete version of the second derivative, $\left(h^{2}=2 m\right) d^{2}=d x^{2}$.

Foreach GQTM the associated step operator $T$ is de ned as a nite sum over elem entary step operators. That is $T={ }_{\mathrm{P}}{ }_{\mathrm{L} ;} \mathrm{T}_{1 \mathrm{~s}}$ where the sum is over all head state labels l L and all qubit state labels $S S$ where $S$ is the set of qubit state labels. For binary qubits $S=10 ; 1 \mathrm{~g}$. $\mathrm{T}_{1 ; s}$ corresponds to the action taken by the GQTM associated with T when the head in state jii sees or reads a qubit in state ji.

The generalization consists in noting that for each $1 ; S T_{1 ; s}={ }_{1 ; s} W_{1 ; s}$ where $\quad$ i;s is a positive realconstant 1 . ForQTM sw ithout the generalization $\quad$ i;s $=1$ for all $1 ; \mathrm{s} . \mathrm{W}_{\mathrm{l}} \mathrm{s}$ is de ned as a sum over all lattice positions of products of pro jection operators, bit and head state change, and head position change operators. The speci c de nition of $W{ }_{\text {lis }}$ appears elsew here 22].

From now on either the $W_{1 ; s}$ or the $T_{1 ; s} w$ illbe referred to as the elem entary step operators for the G Q TM. The reference $w$ iilbe $m$ ade explicit in contexts $w$ here the di erence betw een $T_{l ; s}$ and $W_{l i s}$ is im portant.

Them ain condition im posed on $T$ and its adjoint is that they be distinct path generating in som e basis $B$ which spans $H$. This $m$ eans that iterations of $T$ or $T^{y}$ on any basis state in $B$, generate a path of states that, up to nom alization, are also states in B. Furtherm ore the paths are distinct in that no tw o paths join, intersect, or branch.

A though B can be any basis which spans H, (see 27] for details), B is required here to be the com putation basis, de ned in Section n. A path in B is de ned as a set of states in $B$ ordered by iteration of $T$ or $T^{y}$. If the state $j_{m} ; j_{m} ; S_{m} i=j n ; i i$ is the $m$ th state in some path $i$, then the $m+1$ st and $m$ 1th states in the path are given respectively by $j n+1$;ii $=$
 $j_{n} 1 ; j_{n} ; S_{m} 1$ i. These equations $m$ ust be $m$ odi ed if either $T$ or $T^{y}$ anninilate in ;ii.
$M$ athem atically the requirem ent that $T$ be distinct path generating in the com putation basis, $B$, can be expressed by the condition that $T$ is a direct sum of weighted shifts on $B$. That is, $T=U D={ }_{i} T_{i} P_{i}$ where $U={ }_{i} U_{i}$ is a direct sum of shifts (bilateral, unilateral, adjoint of a unilateral shift, nite, or cyclic) and $D$ is pure discrete with positive real eigenvalues and eigenstates in $B$. These types of shifts correspond respectively to the associated paths being two-w ay in nite, oneway in nite from either end ( $m$ orm 0 ) nite with distinct ends, or cyclic. O ne also has $U={ }^{2} ; \mathrm{W}_{1 ; s}$.

For each $i T_{i}=U_{i} D$ is a weighted shift on a subset $B_{i}$ of $B$ which spans a subspace $P_{i} H$ of $H$ 41]. The projection operators $P_{i}$ are all pairw ise orthogonal. $M$ ore explicitly if




These results, expressed in the com putation basis labels, give for any state which is not a term inal path state,

$$
\begin{align*}
& T j_{m} ; j_{m} ; S_{m} i=D_{m_{n}} ; S_{m}\left(j_{m}\right) j_{m+1} ; j_{m+1} ; S_{m+1} i \tag{2}
\end{align*}
$$

These equations use the requirem ent that $D$ be a local operator in that its values depend only on the state of the qubit at the head location. It is independent of the states of qubits
 connection between the eigenvalues of $D$ and the values of 1 ; is then given directly by $D_{1 ; ~}^{i}(j)=1 ; S(j)$.

If T and $\mathrm{T}^{\mathrm{y}}$ are distinct path generating on B then the direct sum decom position of T $m$ eans that the Feynm an Ham iltonian [40] of Eq. 1 is also decom posable as $H={ }^{P}{ }_{i} H_{i} P_{i}$ where for each $i$,

$$
\mathrm{H}_{\mathrm{i}}=\mathrm{K}\left(\begin{array}{lll}
2 & \mathrm{~T}_{\mathrm{i}} & \mathrm{~T}_{\mathrm{i}}^{\mathrm{Y}} \tag{3}
\end{array}\right):
$$

Since $T_{i}$ is a weighted shift on the path of states in $B_{i}, H_{i}$ is a tight binding $H$ am iltonian on $B_{i}$ and thus in the subspace $P_{i} H$.

A $s$ is noted elsew here 22] $\mathrm{H}_{\mathrm{i}}$ can also be w ritten in the form

$$
H_{i}=K\left(\begin{array}{lll}
2 & U_{i} & U_{i}^{Y} \tag{4}
\end{array}\right)+V_{i}
$$

where K (2 $U_{i} \quad U_{i}^{y}$ ) is, form ally, the kinetic energy associated $w$ th the evolution of the com putation along path i. For the physicalm odel used here it is also the kinetic energy of head $m$ otion on the qubit lattice. (T he kinetic energy depends on the $m$ agnitude but not the direction of the head m om entum on the lattice.)

The potential $V_{i}=K\left(U_{i} \quad T_{i}+U_{i}^{y} \quad T_{i}^{y}\right)$ is a nearest neighbor o diagonalpotentialw ith $m$ atrix elem ents on intemalpath states given by

Since jin ;ii $=j_{m} ; j_{m} ; S_{m} i$ and $D$ is local, $\mathrm{D}_{\mathrm{i}, \mathrm{m}}=\mathrm{m}_{\mathrm{m}} ; \mathrm{S}_{\mathrm{m}}\left(\mathrm{in}_{\mathrm{n}}\right)$.
In Schrodinger evolution under the action of $\mathrm{H}, \mathrm{Eq}$. 1 , the choige of which $\mathrm{H}_{\mathrm{i}}$ is active is determ ined by the initial state ( 0 ). If ( 0 ) is a supenposition of of com putation basis states in just one path $i$, $T$ hen $H_{i}$ is the only active com ponent. If ( 0 ) is a superposition of com putation basis states in di erent paths, then all $H_{i}$ are active for just those paths $i$ in which ( 0 ) has a nonzero com ponent. N ote that in this case the states in the di erent paths evolve coherently.

The sim plest nontrivialchoice forD (other than $D=1$ ) is that the $D$ hastwo eigenvalues 1; where is a positive real num ber between 0 and 1. This will be im plem ented here by lim iting consideration to generalized quantum Turing machines (GQTM s) that have a xed potential associated w ith the read-1 elem entary steps only. A ll other qubit read steps are potential free. Read-1 steps are de ned to be all steps in ; ii ! in +1 ;ii in which an elem entary step term $T_{i ; 1}$ is active (i.e. the qubit at the location of the head is in state jli). $T$ his is accounted for by setting

$$
\begin{equation*}
T={\left.\left.\underset{1}{x} \underset{s \in 1}{X} W_{1 ; s}\right)+W_{1 ; 1}\right]}^{X} \tag{6}
\end{equation*}
$$

## IV.THECOUNTING GQTM

## A. The Step O perator

The counting GQTM serves as an interesting exam ple of the foregoing. B ased on Eq. 6 the step operator for this G Q TM is a sum over seven elem ents or term $s$ (each term inchudes the jsum ):

$$
\begin{align*}
T= & \mathrm{X}^{\mathrm{H}}\left(Q_{0} \mathrm{P}_{0 j} u P_{j}+w Q_{0} P_{2 j} u P_{j}+Q_{1} P_{0 j} u P_{j}\right. \\
& +w Q_{1} P_{2 j} u{ }^{y} P_{j}+Q_{2} v_{x j} P_{1 j} u^{y} P_{j}+w^{y} Q_{2} v_{x j} P_{0 j} u P_{j} \\
& \left.+w Q_{2} P_{2 j} u P_{j}\right)
\end{align*}
$$

The pro jection operators $Q_{1} ; P_{s ; j} P_{j}$ are for the head in state $j 1 i$, the site $j$ qubit in state ji, and the head at site $j$. $w$ is a shift $m$ od 3 on the three head states ( $Q_{m}=Q_{m+1} w m o d 3$ ) and $u$ shifts the head along the lattioe by one site $\left(u P_{j}=P_{j+1} u\right)$. The need for $m$ arkers is accounted for here by choosing the qubits in the lattice to be temary with states j0i; 1 ji ; Ri. Ri is used as a $m$ arker and $j \mathrm{Di} ; \mathrm{jli}$ are used for binary strings. The qubit transform ation operator $v_{x j}=x_{j}\left(\mathbb{P}_{0 j}+P_{1 j}\right)+P_{2 j}$ exchanges the states $j 0 i ; j l i$ and does nothing to the state $2 i$ for the site $j$ qubit.

The adjoint $T^{y}$ is de ned from $T$ in the usual way noting that the operators for the head states, head position states, and qubit states com m ute with one another. N ote that $v_{x j}^{y}=v_{x j}$. This gives

$$
\begin{align*}
& T^{Y}={ }^{X} \quad\left(Q_{0} P_{0 j} P_{j} u^{y}+Q_{0} W^{y} P_{2 j} P_{j} u^{y}+Q_{1} P_{0 j} P_{j} u^{y}\right. \\
& j=1 \\
& +Q_{1} w{ }^{Y} P_{2 j} P_{j} u+Q_{2} P_{1 j} v_{x j} P_{j} u+Q_{2} w P_{0 j} v_{x j} P_{j} u^{Y} \\
& \left.+Q_{2} W^{Y} \mathrm{P}_{2 j} \mathrm{P}_{j} \mathrm{u}^{\mathrm{Y}}\right) \tag{8}
\end{align*}
$$

The term $s$ in $T$ have been chosen so that, besides carrying out the desired operations, $T$ is distinct path generating in the com putation basis. A s de ned $T$ and $_{P} T^{Y}$ satisfy a su cient condition for this [27], nam ely, that $T^{y} T={ }_{\mathrm{P}}^{\mathrm{P}} \mathrm{T}_{1} \mathrm{t}^{\mathrm{Y}} \mathrm{t}$ and $\mathrm{T}^{\mathrm{y}}={ }^{\mathrm{P}}{ }_{\mathrm{t}=1} \mathrm{t}^{\mathrm{y}}$ where t and $\mathrm{t}^{\mathrm{Y}}$ denote term S of T and $\mathrm{T}^{\mathrm{y}}$ in Eqs. 7 and 8.

For this exam ple all steps are potential free except those in which the 5th term is active. For these a potential, given by Eq. 5 , is present as $D_{1 ; 1}=$ for $l=1$. The distribution of potential and potential free steps along a path depends on which of the 7 term $s$ is active for a path state. T he potentialw idth at any path location is given by the num ber of successive iterations forwhich the 5th term is active.

Com parison with Eq. G shows that for this GQTM ( $T=U D$ ) U is a also sum of 7 term $s$ $w$ th $U_{2 ; 1}$ the th term of Eq. $\mathrm{T}^{\mathrm{T}} \mathrm{w}$ th excluded. The other 6 term s of U in the l ; s sum are given directly by Eq. $\bar{\square}$.

To apply this to a speci c exam ple, consider the initialstate, show n in Figure 1, w ith the head in state $j 0 i$ in a w ave packet localized to the left of the origin. Allqubits are in state joi exœept those at sites $0 ; n+1$ which are in state Ri . The in itial head and lattioe qubit state are the path labels for this exam ple. Iteration of $T$ on this state generates in tum all the integers as binary strings of length $n . W$ hen the space between the two $m$ arkers is com pletely led with 1 s , corresponding to the integer $2^{\mathrm{n}} \quad 1$, the last pass of the head changes all 1s to 0 s . The head in state $j 1 i$ then $m$ oves to the right aw ay from the $m$ arker region as the enum eration is com pleted. A $m$ ore detailed description of this process, based on iteration of T , is given elsew here 22].

## B. P otential D istributions

The path potential distribution for the counting GQTM is closely related to the distribution of read-1 steps in all the steps (read-1, read-0, and read-2) obtained by iteration of $T$. This distribution can be represented by a function $R$ from the nonnegative integers to $f 0 ; 1 \mathrm{~g}$ where $R(j)=1[0]$ if the $j$ th step (or $T$ iteration) is a read-1 [read-0 or read-2] step. $T$ he initial state or origin is assum ed to be with the head in state jli at position $n+1$. The location of the origin is not im portant provided all read-1 steps are included.

The read-1 steps occur during a stepw ise search, starting from the units place, for the rst 0 after a string of 1 s . B ased on this $R$ would be expected to be related to the function $R$ from the nonnegative integers to the nonnegative integers such that, in the binary string for $j, R(j)$ gives the num ber of 1s occurring before the rst 0 . Because of this, the properties of $R$ can be used to obtain a usefulexpression for $R$.

The range sequence of $R$, which is $0 ; 1 ; 0 ; 2 ; 0 ; 1 ; 0 ; 3 ; \quad$, is known as the hierarchical sequence 39]. It can be expressed recursively 22] by the pair of recursion equations; $\mathrm{R}_{\mathrm{N}}=$ $S_{N}{ }_{1} N ; S_{N}=R_{N} S_{N} 1$ for $N=1 ; 2$; $\quad w$ ith $S 0 . R_{N}$ is the rst $2^{N}$ elem ents ofR. $R$ is a generalized substitution sequence under the substitution nule $n!0 n+1$ for $n=0 ; 1 ; 2$;

The generalization denotes the fact that, contrary to the literature de nitions 6, 42, 43], the alphabet is in nite.

The recursion relations for $R$ also hold for $R$ if $N$ is replaced $w$ th $\underline{N}$ where $\underline{N}$ denotes the string of num bers $01^{\mathrm{N}} 0^{\mathrm{N}+1}$. Here $1^{\mathrm{N}}$ and $0^{\mathrm{N}+1}$ denote strings of N 1 s and $\mathrm{N}+10 \mathrm{~s}$. $T$ hat is, for $N=1 ; 2$;

$$
\begin{equation*}
R_{N}=S_{N} 1 \underline{N} ; S_{N}=R_{N} S_{N 1}: \tag{9}
\end{equation*}
$$

$w$ here $S_{0}=\underline{0}$.
This equation gives the distribution of read-1 steps in all steps associated w ith enum erating the rst $2^{\mathrm{N}}$ integers. An example for $\mathrm{N}=6$ is given elsew here 22]. The explicit locations ofbands of read-1 steps can be obtained by noting that the num ber ofelem ents in $S_{N}$ and $R_{N}$ is given respectively by $2^{N+3} \quad 2(\mathbb{N}+3)$ and $2^{N+2} \quad 2$. The num ber of read- 1 bands is equal to $2^{N}{ }^{1}$.

The relation of the read-1 step distribution to the potential distribution in the tight binding H am iltonian, Eq. 囲, for the path corresponding to enum erating the rst $2^{\mathrm{N}}$ integers, can be obtained from $\mathrm{R}_{\mathrm{N}}$. Extend $\mathrm{R}_{\mathrm{N}}$ to a two way in nite sequence by adding 0 s to both ends. De ne a function $D_{i}$ on the spectrum of $D$ by $D_{i, m}=D_{i}(m)$. The function $D_{i}$ is related to the extended $R_{N}$ by

$$
\begin{equation*}
D_{i}=1+(1) R_{N}: \tag{10}
\end{equation*}
$$

. From this the $m$ atrix elem ents of $V_{i}$, Eq. ${ }^{\text {, }}$, are given by

$$
\left.m^{0}{ }^{0} V_{i} \dot{m} i=K(1 \quad) \mathbb{R}_{N}(m)_{m} 0_{m+1}+R_{N}\left(\begin{array}{ll}
m & 1 \tag{11}
\end{array}\right)_{m^{0} m_{m}} 1\right]:
$$

Eq. 11 show sthat the o -diagonal potential barrier associated $w$ th a band of $n 1$ s at path sites a; $\quad ; a+n \quad 1$ with $0 s$ on both sides $\left(i, e_{N} R(j)=1\right.$ if $a \quad j a+n \quad 1$ and $\left.R_{N}(a \quad 1)=R_{N}(a+n)=0\right)$ extends from sites a to $a+n$. $T$ he potentialbarrier has a core of 11 sites of height 2K ( ) anked by single site potentials of height $\mathrm{K}(1 \quad)$ at sites a and $\mathrm{a}+\mathrm{n}$. This is the case whether these sites correspond to in itial or nal states in the $m$ atrix elem ents of Eq. 11. N ote that a potential is associated $w$ ith the site $a+n$ for which $R_{N}$ has value 0. If $n=1$ the barrier is two sites $w$ ide and has a height of $K(1)$ as no core is present. The potential distribution given by Eq. 11 for $N=6$ is shown in $F$ igure 2.

Figure 2 is a good ilhustration of the general property of the distribution, that barriers that are two sites $w$ ide $(n=1)$ are the $m$ ost com $m$ on as $1=2$ the barriers are of this type. $O$ ne half the rem aining barriers are 3 sites $w$ ide $n=2$, and $1=2$ those rem aining are 4 sites wide ( $n=3$ ), etc..

There are $m$ any other possible initial states and paths $w$ th associated tight binding H am iltonians besides that given in F igure 1. D iscussion of these, and the collection of paths into equivalence classes, is discussed elsew here 22].

## C. Transfer M atrix

Follow ing E rdos and H emdon [18], solutions for tight binding H am iltonians, such as that given by Eq. 4, can be written as $=\mathrm{I}^{+}$II ${ }^{+}$III where I and III are the states
coresponding to the path boundary potential free regions and is is the state in the path region containing the potentials. For exam ple if the path regions for $j<0$ and $j>n$ are potential free (integers label path states) then

$$
\begin{gather*}
I=X_{j=1}^{X^{1}}\left(A e^{i k j}+B e^{i k j}\right) j \dot{j} i \\
I I I=X_{j=n+1}^{X}\left(F e^{i k j}+G e^{i k j}\right) \dot{j} i i \tag{12}
\end{gather*}
$$

Here $j$ is the path state label and $k$ is the $m$ om entum in the potential free regions.
$T$ he form of it depends on the form of the potential. For a single barrier corresponding to a band of N read-1 sites extending from site a to a $+\mathrm{N} \quad 1$,

$$
\begin{align*}
I I= & \left(C_{1} e^{\text {iha }}+D_{1} e^{\text {iha }}\right) \dot{j i} i+{ }_{j=a+1}^{a+\lambda^{N} 1}\left(C_{2} e^{i l j}+D_{2} e^{i l j}\right) \ddot{j} i i \\
& +\left(C_{3} e^{\text {ih }(a+N)}+D_{3} e^{i h(a+N)}\right) j \dot{j}+N i:
\end{align*}
$$

If the energy is below the barrier height of $2 \mathrm{~K}(1 \quad)$, which is the case of interest here, then $l$ is replaced by $i l$. If the energy is below $K(1 \quad)$ then the $m$ om entum $h$ is replaced by ih. If several potentials are present II is a sum of term sof the form of Eq. 13.

The four complex coe cients A;B;F;G are completely determ ined by boundary conditions for the case under study and the properties of the transfer m atrix. For exam ple if initial states are required to be localized in region I ( $F$ igure 1), then $G=0$ as there is no incom ing head $m$ otion in region III.
$T$ he transfer $m$ atrix $Z$ relates the coe cients F ; G to A ; B according to 8

$$
\begin{aligned}
& \mathrm{F} \\
& \mathrm{G}
\end{aligned}=\mathrm{Z}_{\mathrm{B}}^{\mathrm{A}} \begin{aligned}
& \text { ! }
\end{aligned}
$$

Z is a unim odular (determ inant=1) $2 \quad 2 \mathrm{~m}$ atrix which also satis es [18]

$$
\begin{align*}
& \mathrm{Z}_{11}=\mathrm{Z}_{22} \\
& \mathrm{Z}_{12}=\mathrm{Z}_{21}: \tag{14}
\end{align*}
$$

For a string of potentials the transfer $m$ atrix connecting the state on the right to the state on the left is the product of the transfer $m$ atrices for each of the potentials [18; 20]. If the potential distribution is given by a recursion relation, such as that of Eq. G, then the transfer $m$ atrix $Z_{N}$ for the potential distribution corresponding to $R_{N}$ is given by the recursion relations

$$
\begin{align*}
\mathrm{Z}_{\mathrm{N}} & =\mathrm{W}_{\mathrm{N}} \mathrm{X}_{\mathrm{N}} 1 \\
\mathrm{X}_{\mathrm{N}} & =\mathrm{X}_{\mathrm{N}} \quad \mathrm{~W}_{\mathrm{N}} \mathrm{X}_{\mathrm{N}} \quad 1 \tag{15}
\end{align*}
$$

w th $\mathrm{X}_{0} \dot{\mathrm{I}}_{1}=\mathrm{e}^{2 \mathrm{ik}}$ and $\mathrm{X}_{0} \dot{\mathrm{I}}_{2}=0$. Eq. 14 holds for $\mathrm{X}_{0} . \mathrm{W}_{\mathrm{N}}$ is the transfer m atrix for the potential corresponding to the sequence $\underline{N}=01^{\mathrm{N}} 0^{\mathrm{N}+1}$. A s noted earlier this corresponds to a potential barrier w ith a core width of N 1 sites anked on each side by a one-site
potential half the core height. P otential free regions of 1 site and $N+1$ sites surround the barrier. N ote that the order ofm atrix m ultiplication in Eq. 15 is the inverse of the order in which term s appear in the sequence of Eq. G .

This use of recursion relations has the advantage that in order to obtain the elem ents of the $m$ atrix $Z_{N}$, only polynom ially $m$ any $m$ atrix $m u l t i p l i c a t i o n s$ are needed. If $Z_{N}$ is obtained from the $m$ atrices associated $w$ ith each potential barrier in the distribution, then exponentially $m$ any $m$ atrix $m$ ultiplications are required.

From Eq. 15 one sees that the only $m$ atrices needed in explicit form (other than $X_{0}$ ) are the $W_{m}$ form $N$. These can be obtained explicitly (see also [18]) by setting ( $E H_{i}$ ) $=0$ where $H_{i}$ is given by Eqs. 4 and 11, and the state is given by Eqs. 2 and 4. A set of linear equations is obtained by setting the coe cients of each state j; ii equal to 0 . that is

$$
\begin{align*}
& j^{0} \tag{16}
\end{align*}
$$

Because $H_{i}$ contains nearest neighbor interactions only, just 3 term $s$ in the $j^{0}$ sum, $j^{0}=j ; j 1$ contribute.
$T$ he linear equations so obtained can be used to derive the $m$ atrix elem ents of $W_{m}$ for $\underline{m}=01^{m} 0^{m+1}$. A brief summ ary of the derivation is given in the A ppendix. For energies below the potential core height (i.e. less than 2K (1)), they are

$$
\begin{align*}
& W_{m} \dot{\boldsymbol{j}}_{1}=\frac{e^{i k(m+2)}}{2 i \sin k \sinh l}\left[e^{2 i k} \sinh l m \quad 2 e^{i k} \sinh l(m \quad 1)+{ }^{2} \sinh l(m \quad 2)\right] \\
& \left.W_{m} \dot{\mathbf{j}}_{2}=\frac{e^{i k m}}{2 i \sin k \sinh l}\left[\begin{array}{lll}
\sinh l m & 2 \sinh l(m & 1) \operatorname{cosk}+{ }^{2} \sinh l(m
\end{array} \quad 2\right)\right] \tag{17}
\end{align*}
$$

where the m om enta $1 ; \mathrm{k}$ are related by $2 \mathrm{~K}(1 \quad \operatorname{cosk})=\mathrm{E}=2 \mathrm{~K}(1 \quad \cosh 1)$. For the ank potentials or those for $m=1$, $E=K\left(2\left({ }^{2}+2 \cos 2 h+1\right)^{1=2}\right)$. H ow ever, the m om entum h, Eq. 13, does not appear in the above. These equations can be show $n$ by explicit calculation to hold for $m=1$ and $m=2$ as well as for larger $m$. O ne also has $\mathrm{W}_{\mathrm{m}} \dot{\dot{1}}_{1}=\mathrm{W}_{\mathrm{m}} \dot{\dot{2}}_{2} ; \mathrm{W}_{\mathrm{m}} \dot{\underline{2}}_{1}=\mathrm{W}_{\mathrm{m}} \dot{\dot{1}}_{2}$; and $\mathrm{W}_{\mathrm{m}}$ is unim odular.

## V.ENERGYBANDSAND GAPS

A s is well known 45,1920] the distributions of energy bands and gaps for the in nite 1D periodic system, w ith a unit cell satisfying the problem being considered, can be obtained from a plot of $T r Z_{N}$ as a function of the $m$ om entum $k$. Regions for which $\mathfrak{J} r Z_{N} j 2$ correspond to energy bands; regions with $\mathfrak{J} r Z_{\mathrm{N}} \mathrm{j}>2$ correspond to energy gaps. As the m ain interest in the paper is in bound states, k is restricted to be less than arcoos. The in nite periodic system is referred to as the associated periodic system.

Test calculations show that except for values of very close to 1 , the values of $\mathrm{TrZ}_{\mathrm{N}}$ uctuate extrem ely rapidly betw een astronom ically large positive and negative values (of the order of $10^{M}$ where $M$ is very dependent on and $N$. Forvalues of appreciably di erent from 1 and values of N of order 10, M has values greater than 200. It is thus necessary to determ ine values of the two free param eters K ; that are reasonable physically. To do this it is necessary to assign a spacing to the lattice qubits. Then the dim ensionless
m om enta $1 ; \mathrm{k}$ are related to the usualm om enta $\mathrm{l}^{0} ; \mathrm{k}^{0}$ by $\mathrm{k}=\mathrm{k}^{0} ; \mathrm{l}=\mathrm{l}^{0}$. The form of K is obtained from the fact that if $\mathrm{T}=\mathrm{Y}$, the bilateral shiff on the lattioe, then $\mathrm{H}, \mathrm{Eq} . \mathrm{T}^{1}$, is the sym $m$ etrized form of the second derivative on the lattioe. This gives

$$
\begin{equation*}
K=\frac{h^{2} c^{2}}{2 m} \tag{18}
\end{equation*}
$$

$w$ here $m$ is the $m$ ass of the head in energy units $\left(m c^{2}\right)$.

$$
\begin{align*}
\text { Since } V=2 K(1 \quad) \text {, with }=1 & \\
& =\frac{2 m \vee{ }^{2}}{\mathrm{~h}^{2} \mathrm{c}^{2}}: \tag{19}
\end{align*}
$$

For electron system $\mathrm{s}, \mathrm{m}$ is of the order of the electron m ass, V is a few electron volts, and is m easured in A ngstrom s. Taking m equal to 2 electron m asses, $=1 \mathrm{~A}$, and $\mathrm{V}=2 \mathrm{ev}$ gives ' 0:001 or ' 0:999

The $m$ ethod used for calculation of $\mathrm{Tr} \mathrm{N}_{\mathrm{N}}$ consists of using the recursion relations, Eq. [15, to obtain $Z_{N}$ and then taking the trace. The well know $n m$ ethod of using trace $m$ aps [42] [12], is not used because it is m ore e cient to obtain directly the matrix Z n and then take the trace rather than by use of the trace $m$ ap relations. In partioular, obtaining $Z_{N}$ directly from Eq. 15, using Eq. 14, and then taking the trace requires a num ber of scalar $m$ ultiplications proportional to $N$. Use of the trace $m$ ap requires a num ber of scalar m ultiplications proportional to $\mathrm{N}^{2}$.

Energy bands and gaps were calculated as a function of the dim ensionless $m$ om entum k for several di erent values of and N . The results for $=0: 999$ are given in F igure 3 for $\mathrm{N}=10$; 15; 18 as three bands of vertical lines connecting horizontal line segm ents or points. The upper or low er horizontal line segm ents or points represent respectively energy bands or energy gaps. P oints represent bands or gaps whose width is of the order of the values of the increm ent or spacing $k$ used to $m$ ake the calculations.

The range of $m$ om entum show $n$ is from $k=0: 0223$ to $k=$ arcoos. The lower lim it is chosen because, to the accuracy of the calculations, there are no energy bands in the region $\mathrm{k}<0: 0223$ in which $\mathrm{TrZ}_{\mathrm{N}}$ increases rapidly to very large values. Each band shows the result of calculations using about 2800 equally spaced grid points which gives $\mathrm{k} \quad=5600$.

The lower band for $N=10$ show $s$ that $m$ ost of the $m$ om entum region 0:0223 k arcoos $=0: 0447$ is covered by energy bands separated in $m$ ost cases by very narrow gaps. The w idest gap is at $\mathrm{k}^{\prime} 0: 033 \mathrm{w}$ ith sm aller gaps at $\mathrm{k}^{\prime} 0: 025 ; 0: 029 ; 0: 038$, and $0: 043$.

The m iddle band for $\mathrm{N}=15$ shows that the w ide energy bands for $\mathrm{N}=10$ are split into $m$ any smaller bands with intervening gaps. Gaps which were already present at $\mathrm{N}=10$ continue to be present. This splitting continues for increasing N as is shown by the upper band for $\mathrm{N}=18$. The width and positions of the larger gaps at $k^{\prime} 0: 043 ; 0: 038 ; 0: 033 ; 0: 029 ; 0: 025$ are $m$ aintained. The bands also show that as $N$ increases the num ber of bands increases greatly. H ow ever the band w idths decrease even faster so that the fraction of the $m$ om entum region associated with energy bands, although sitll large, decreases as N increases.

The distribution of bands or band density is shown by the spacing or density of the vertical lines. For exam ple for $\mathrm{N}=18$ the density is high in the dark regions of the band, such as around $k \quad 0: 024$ and $0: 036$. It is low in the regions of the $w$ ide gaps.

Calculations were not $m$ ade for values of $N>18$ because the range and uctuation of values of $\operatorname{TrZ}_{\mathrm{N}}$ becom es so extreme that the accuracy of calculations that can be made w th a reasonable am ount of time and e ort becom es questionable. Even at $\mathrm{N}=18$ high resolution calculations (to be discussed later) over sm all m om entum regions are needed to resolve individual bands. Recall that the results shown give the energy band and gap structure for an in nite periodic structure $w$ th a unit cell of $2^{\mathrm{N}}{ }^{1}$ potentials $w$ ith a width and location distribution given by Eq. 9 . Thus for $N=18$, about 128;000 potentials are present in the unit cell.

In all gures except $F$ igure 1, the values of the $m$ om entum used in the abcissa are larger than the actual values by a factor of 1000. They are also dim ensionless. T his has the advantage that the bands in $F$ igure 3 are valid for any values ofm; $V$; that give $=0: 001$ (Eq. 19) or $=0: 999$. O ne set is the values chosen for the electron range. A nother set in the nuclear range (probably im possible to realize) that gives 0:001 is $m$ equal to the proton m ass, $\mathrm{V}=1 \mathrm{M}$ ev and $=3 \mathrm{~F} .\left(1 \mathrm{~F}=10^{13} \mathrm{~cm}\right)$. For the values chosen in the electron range the $m$ om entum range show $n$ in the gure corresponds to an energy range of from 1 to 2 ev .

It is useful to explore a w ider variation of param eters, such as larger values of m; , or V which give di erent values of . Choosing values which increase values of gives one m ore latitude in a choice of physical m odel param eters. For this reason calculations were also m ade for larger by a factor of 10. The results are show n in F igure 4 for $=0: 99$ for the sam e values of $N$ used in $F$ igure 3. The mom entum range is cut $o$ at $k=0: 069$ as there do not appear to be any bands below the cuto .

C om pared to the results for $=0: 999$, Figure 4 show s a great increase in the fraction of the $m$ om entum region occupied by energy gaps. There are large gaps around values of $\mathrm{k}=0: 084$ and 0:10 and especially 0:12. There are m any m ore energy bands present than are show $n$ in $F$ igure 3 for the sam e value of $N$. But the widths are so $m$ uch sm aller that the fraction of the region alloted to energy bands is $m$ uch less. This is especially pronounced in the bands for $N=15$ and $N=18$ where energy bands show as points only. For these values of $N$, the $m$ axim um w idth of any energy band is only about $0: 0002$. The calculations for $\mathrm{N}=15$ and $\mathrm{N}=18$ should only be taken as giving a rough indication of the bands present. Use of ner grids in the calculations would be expected to show $m$ ore bands of very m all w idths in the high density band regions than are shown in the gure. The large gaps would be expected to rem ain.

Increasing the value of by another factor of 10 to give $=0: 9$ gives the results show $n$ in F igure 5. They were obtained using a grid w ith over 7000 equally spaced points w ith a low m om entum cuto at $0: 166$. The values of N used are sm aller than those in the preceding gures because the uctuations in the values of $T Z_{N}$ are so large.
$T$ he calculations show that very few energy bands are present and except for $\mathrm{N}=6$ the widths are pointlike. For $N=6$ the band grouping appears to be hierararchical in that pairs of doublets are grouped into pairs of quartets which are in tum grouped into octets. The appearance of the band at $k$ ' 0:196 as a singlet instead of a doublet $m$ ay be a consequence of the nite resolution of the calculations. The gaps between the groups increase as the group size increases. There are indications that this structure m ay be preserved for $\mathrm{N}=8$ and possibly for $\mathrm{N}=10$. H ow ever, each band splits up into m any m aller bands as N increases. M ore detailed calculations w ith extrem ely ne grids would be needed to check
this.
The reason for the low m om entum cuto s in the appearance ofbands is not clear. T hey do not appear to be associated w th the height of the narrow est barriers ( $1 / 2$ of the total), i.e. those with height $K(1 \quad)$. For these barriers the corresponding values of the $m$ om entum at which the energy equals the barrier height (cosk $=(1+\quad)=2$ ) are 0:0316; 0:100; 0:317 for $=0: 999 ; 0: 99 ; 0: 9$ respectively. These values are appreciably higher than the values at which bands rst appear.

## VI.LANDAUER RESISTANCE

Interest in the Landauer Resistance [17,18], de ned as the ratio of the re ection probability to the transm ission probability through a nite sequence of potentials, is based on the fact that for 1D electronic system $s$, it is a $m$ easure of the transm ission of the electron through the system.

From the standpoint of this paper the Landauer R esistance (LR) is of interest because the reciprocal, $1=(1+L R)$, is the probability oftransm ission through the potentialsequence. For any path ofstates for a G TM, the reciprocal is a m easure of the probability of com pletion of the quantum com putation as it refers to the transm ission of a wave packet from one end of the path to the other through potentials associated w ith the path states. For the counting GQTM it is a measure of the probability of completion of the counting $w$ th potentials associated w th read-1 steps only.

Landauer 23] has em phasized that re ection from background potentials associated w ith each step of a quantum com putation degrade the com putation due to multiple re ections from and transm issions through the potentials. In particular for energies below the potential height the transm ission would be expected to decay exponentially as the padket $m$ ust tunnel through each of the potentials,

There are indications that this $m$ ay not be true for potential sequences which are not random. Forexam ple it hasbeen shown 19,20] that for $T$ hue M orse, F ibonnaci, and periodic sequences in the $K$ ronig-Penney $m$ odel, the Landauer Resistance uctuates rapidly $w$ ith energy between very high values \gg 1 and very low values \ll 1. In addition high values are associated w thenergy gaps in the in nite associated periodic system; low values are associated w th energy bands.

For these reasons the Landauer Resistance (LR) has been calculated for the counting GQTM for various values of $N$ and as a function of the dim ensionless $m$ om entum $k$. The calculations are done using the result that the LR is given by 18]

$$
\begin{equation*}
\mathrm{LR}=\mathrm{z}_{\mathrm{N}} \dot{\mathbf{1}}_{2} \mathfrak{J} \tag{20}
\end{equation*}
$$

where $Z_{N}$ is given by Eq. 15. The results are shown in gures that show the functional dependence of the log (base 10) of the Landauer R esistance ( log LR ) on the $m$ om entum . $T$ he $m$ om entum units are dim ensionless.

The results for $=0: 999$ and $N=10$ are shown in Figure 6. The enery band and gap structure for the associated periodic system is reproduced at the bottom of the gure. The calculations show a rapidly uctuating log LR w th large maxim a at m om entum values corresponding to energy gaps. The heights of these large $m$ axim a appear to be correlated
w ith associated gap widths; w ide gaps have greater m axim a than narrower ones. A lso the general trend of the values such as the height of the $m$ axim $a$, is tow ards low er values as the m om entum increases. B oth these features were noted by R oy and K han 19,20]. H ow ever for the sm aller maxim a, which occur in regions of energy bands of fairly uniform width separated by narrow gaps, the opposite appears to be the case in that the m axim a appear to be associated w ith energy bands. In addition log LR has shanp spikes to very low values at the regions of these narrow gaps.

An interesting feature of the results is that for $m$ ost values of the $m$ om entum $\log \operatorname{LR}$ is less than 0. A value of 0 corresponds to a $50 \%$ probability of transm ission through the potentials. Thus for this case the probability of com pletion of the quantum com putation is > 50\% for m ost m om enta. For selected values the probability is close to $100 \%$. These low values are very likely correlated w ith the result that $m$ ost $m$ om enta are in energy bands $w$ ith only a small fraction of the $m$ om entum region taken up $w$ ith gaps.
$F$ igure 7 show s a higher resolution plot of $\log L R$ for a portion of the $m$ om entum region. It show s very clearly the association of the sharp minim a to band edges. A study of the actual com putation points for the gure shows that the $m$ inim a are associated with the upper edge of a band just below a gap and not w th the low er edge of a band just above a gap. A lso the depth of the $m$ inim a appear to depend on the width of the associated gap in that in general the depths are $m$ uch less for wider gaps than for narrow er ones. For exam ple the $m$ inim um with the relatively wide gap at $k=0: 0355$ is higher than the sharp spike m inim a on either side w th relatively narrow gaps. The minim um associated w the the even wider gap at $\mathrm{k}=0: 038$ has alm ost disappeared.

The results of a calculation of log LR for the sam e value of but for a larger value of $\mathrm{N}=18$, are shown in F igure 8. Just as the band spectnum is $m$ uch $m$ ore nely divided log LR uctuates much $m$ ore rapidly and violently. For the purposes of clarity the plot is cut o at values of log LR > $20\left(\mathrm{LR}>10^{20}\right)$. Themain reason is that the interest here is in the behaviour of log LR around 0 and not how high the values can go.

The results show that there are a great num ber of values of the $m$ om entum for which $\log L R$ is 0 or less. H ow ever there are also a large num ber of uctuations to much higher values. Because of the nely divided nature of the spectrum and extrem e violence of the uctuations, the gure should be taken only as an approxim ate indication of the dependence of log LR on the m om entum .

A higher resolution calculation over the range 0:032 k 0:033, F igure 9, show sery clearly the preponderance of values at or below 0 . as well as the rapid uctuation to large $m$ axim a. The heights of the $m$ axim a are clearly correlated $w$ th the $w$ idths of the associated gaps. H ow ever, the individual sm all uctuations are barely resolved. T he heights of the peaks also show a regularity that can be correlated with the widths of the potentials in the distribution. T he regularity appears to be correlated with the hierarchical structure of the sequence given by Eq. 9 .

A very high resolution calcuation over a very sm allm om entum region of 0:03225 $k$ $0: 03228$ for $=0: 999 \mathrm{~N}=18$ is shown in $F$ igure 10. The gure show s very clearly the correlation betw een the decrease in the depths of the $m$ inim a and the increase in the $w$ idths ofthe associated gaps in the band spectra. Forexam ple the gap at $k=0: 032261$ is su ciently w ide that the associated m in m um in log LR has just about disappeared $w$ th only a slight dip present. Shallow minim a are associated with the narrower gaps at $k=0: 032253$ and
$k=0: 032269$. The gure show $s$ also that band $w$ idths are m uch m ore uniform than gap w idths which vary w idely. $T$ his point was noted before for sm aller values of $N$.

These gures show that there are fairly $w$ ide regions of the $m$ om entum where, exaept for a few sharp spikes, $\log \mathrm{LR} \quad 0$. It is notew orthy that this corresponds to transm ission through m ore than 128;000 potentialbarriens $w$ ith the energy below the barrier height for $1 / 2$ these potentials for $0: 0316 \mathrm{k}$ arccos. For $\mathrm{k} \quad 0: 0316$ the energy is below the barrier height for all the potentials. It is possible that the high transm ission is due to the quasiperiodicity of the potential distribution; how ever m ore w ork is needed to test this possibility.

In order to show the dependence of $\log L R$ on for $x e d N$, calculations were $m$ ade for $N=10$ and $=0: 99$. this value is larger by a factor of 10 than that used so far. It corresponds to the electron regim e w ith larger param eters in Eq. 19 to give $=0: 01$. The results are shown in F igure 11.

The gure show s very clearly the correspondence betw een maxim a in log $L R$ and gaps in the spectrum . Large gaps are associated w ith high peaks and sm all gaps w ith sm all peaks. A lso the correlation betw een the peak heights and the hierarchical stnucture of R , Eq. Gr, appears to be present. In regions w here the band and gap widths are $s m a l l, \log L R$ uctuates between values of about 1 and 2 or less. O $n$ average the values of $\log L R$, even in sm all gap regions, are higher than for $=0: 999$. This is to be expected as sm aller values of correspond to larger values of the potential. O n average the transm issivity is appreciable as there are extended regions where the values of $\log \mathrm{LR}$ are around 0 .

C alculations for larger by another factor of 10 to $=0: 1(=0: 9)$ are shown in Figure 12 for $N=8$. The extrem e violence of uctuations in the values of $\log L R$, even for the relatively low value of $N=8$ is evident. This is to be expected since higher values of corresponds to higher values of the potential ( $w$ ith $m$ and $x e d$ ). A lso since $m$ ost of the space is occupied by gaps, $\log L R$ has very high values and approaches 0 only in the regions of narrow bands.

A high resolution calculation for $=0: 9$ and $\mathrm{N}=8$ over a small portion of the m om entum region $0: 40 \quad \mathrm{k} \quad 0: 415$ is shown in F igure 13 . T he gure show s very clearly the association ofm inim a in the LR w ith upper edges of energy bands and the loss of minim a w ith increasing gap width. The gap including the value of $k=0: 408$ is so w ide that the associated $m$ inim um in log LR is com pletely gone. A lso the values of the $L R$ in the sm all m om entum region show n in the gure are betw een 10 and 100 on average w ith values at or below 1 (logLR 0 ) occuring only rarely.

## V II. D ISC U SSIO N

To sum $m$ arize, the $m$ ain characteristics of the band spectra show $n$ here inchude the relative uniform ity ofband widths com pared to gap w idths over the bound state m om entum regions. This is especially apparent in $F$ igure 3 . This gure and $F$ igure 4 suggest that uctuations in bands w idths do appear to increase som ew hat as increases.

The gures also show that as increases the gap widths and the fraction ofm om entum range occupied w ith gaps increases greatly. For $=0: 001 \mathrm{~m}$ ost of the k region is occupied by bands. For $=0: 01$ a large fraction is taken up by gaps and for $=0: 1 \mathrm{alm}$ ost all the region is gaps w ith a few very narrow bands present.

Figures 3-5 show that for xed values of as N is increased, energy bands are split into increasing num bers ofbands with decreasing $w$ idths. $G$ aps that exist for a given value of $N$ appear to be preserved as N is increased above the given value. This suggests but does not prove that in the lim it of $N=1$, for each the spectrum of the tight binding $H$ am iltonain is singular continuous and is a C antor set. H ow ever, the proofs in the literature [ [4, $]^{2}$ ] do not hold here as the generalized substitution sequence of Eq. 9 is not prim titive.

The values oflog LR also uctuatew idely over them om entum rangew th the uctuations very dependent on the values of and N. Shanp minim a are located at or near band-gap boundaries w th m orem inim a located at or near gap-above-band edges than at ornearband-above-gap edges. The reason for the location ofm inim a at or near band gap boundaries is not clear. It is worth noting that, based on the properties of $Z_{N}$, Eq. 14, LR $=\mathcal{Z}_{\mathrm{N}} \dot{\mathrm{i}}_{\mathrm{i} 1}{ }^{?} 1$. At the boundaries $\mathfrak{j} r Z^{N}=2 j=1$. This gives

$$
\begin{equation*}
L R=\dot{\mathcal{F}}\left(Z_{N} \dot{\mathrm{~L}}_{; 1}\right) \hat{\jmath} \tag{21}
\end{equation*}
$$

at the boundaries. $=(\mathrm{x})$ denotes the im aginary part of x .
A nother aspect of the $m$ in im a is that none are associated $w$ ith boundaries of su ciently $w$ ide gaps. The gures show that in alm ost all cases the depth of the $m$ inim um in log LR is very dependent on the $w$ idth of the associated gap. If the gap is narrow, the $m$ in im um is deep. As the gap becom es wider the associated minim um becom es shallower until it disappears for su ciently wide gaps. An exam ple of this where the minim a has alm ost disappeared is the gap just below $k=0: 03227$ in $F$ ig 10. O ther exam ples can be found in the other gures.

O ne consequence is that for w ide gaps the m axim a in the LR appear to be centered over the gaps. For narrow gaps there is an associated minim um in the LR. For these cases the $m$ axim a in the LR appear to be centered over the bands and not the gaps.

These results di er from those obtained by R oy and K ahn 19,20, for the T hue M orse lattice in that they found allm axim a in the LR centered on the gaps irrespective of the gap widths. The reason for this di erence is not clear. T he results obtained here do agree w ith those of $R$ oy and $K$ han in that the larger LR maxim a are associated with wide gaps, and the $s m$ aller $m$ axim a are associated $w$ th narrow er gaps. A s noted, here the sm aller $m$ axim a tend to be centered over the bands and not the gaps.

A s is well known the Landauer Resistance is a m easure of the transm ission through a sequence of potentials. For the case at hand it is a m easure of the com pletion probability for the counting generalized quantum Turing $m$ achine to enum erate the nonnegative integers up to $2^{\mathrm{N}} \quad 1$. H ow ever the strong dependence of the LR on $\mathrm{k} m$ eans that care $m$ ust be taken in its use. For exam ple Figure 1 show s an intial state represented as a wave padket over di erent head lattice positions w ith a xed lattice qubit state. Transform ed to m om entum space the initial state is in essence a wave packet over the head $m$ om entum $k w$ th the sam $e$ xed head intemal state and lattice qubit state. T hat is $=\mathrm{c}_{\mathrm{k}} \mathrm{j} ; \mathrm{k} ; \mathrm{Sidk}$ where $\mathrm{j}_{\mathrm{i}} \mathrm{k} ; \mathrm{Si}$ is a state for the head in state $l$ and $m$ om entum $k$ and the qubit lattice in state j $\mathrm{j} i$.

Linearity of the Schrodinger Equation gives the result that, for each com ponent state $\mathrm{c}_{\mathrm{k}} j ; \mathrm{k} ; \mathrm{S}$ i, the transm ission and re ection coe cients are given respectively by

$$
F=\frac{\mathrm{C}_{\mathrm{k}}}{\mathrm{Z}_{\mathrm{N}} \dot{\dot{\underline{1}} ; 2}}
$$

$$
\begin{equation*}
B=\frac{Z_{N} \dot{\xi}_{1} q_{k}}{Z_{N} \dot{\xi}_{2}} \tag{22}
\end{equation*}
$$

Here Eqs. 12 and 13 were used along w th the properties of $Z_{N}$, Eq. 14. The coe cient $G=0$ as there is no incom ing com ponent in region III. A s the results in Section V7 show, the coe cients $F$ and $B$ are very dependent on $k$. O fcourse the $L R$, given by $L R=\beta j^{2}=F^{2} j$ is independent of the norm alization to $\mathrm{c}_{\mathrm{k}}$ show n in Eq. 22.
$M$ ore general linear superpositions in the initial state are possible. For exam ple the $m$ ost general in itial state for the counting GQTM is given by $=\operatorname{lis}^{2} \quad C(1 ; k ; S) j ; k ; S i . E a c h$ com ponent in the $S$ and lsum scorresponds to a di erent input state and a di erent quantum com putation. This ability ofquantum com puters to carry out sim ultaneously com putations on di erent input states i.e. parallel quantum com putation was rst described by D eutsch 28].

From the perspective of this paper an interesting aspect of the above is that Schrodinger evolution w ith one H am iltonian, Eq. $]_{\text {for the system is equivalent to a linear supenposition }}$ of di erent Schrodinger evolutions each with a di erent tight binding $H$ am iltonian. This follows from the fact that in general for each com ponent in the $1 ; S$ sum, the potential distribution on the corresponding state path depends on $\ddagger \mathfrak{j}$ i and on 7 il. This is an exam ple of a linear superposition of the action of com ponent H am iltonians in the decom position of the Feynm an H am iltonian, Eq, 团 into a sum over tight binding H am iltonians, Eq. $\mathrm{B}_{3}$.

## ACKNOW LEDGEMENTS

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## APPEND IX

A s noted in the text around Eq. 16 , solution of ( $\mathrm{E} \quad \mathrm{H}$ ) $=0$ gives a set of linear equations, one for each path state $\mathrm{j} i$. In regions of constant potential or that are potential free, $=1$, the linear equations have the sam eform :

$$
\begin{equation*}
(j \mathrm{X} Y)(\mathbb{E} \quad 2 \mathrm{~K})+\mathrm{K} \quad(\mathrm{j} \quad 1 \mathrm{XY})+\mathrm{K} \quad(\mathrm{j}+1 \mathrm{XY})=0: \tag{23}
\end{equation*}
$$

Here ( $\mathrm{j} \mathrm{X} Y$ ) is a shorthand notation for $\mathrm{X} \mathrm{e}^{\mathrm{iqj}}+\mathrm{Y} \mathrm{e}^{\mathrm{iqj}}$ where $\mathrm{X} ; \mathrm{Y}=\mathrm{A} ; \mathrm{B} ; \mathrm{C}_{\mathrm{i}} ; \mathrm{D} \mathrm{D}_{\mathrm{i}} ;$ or $\mathrm{F} ; \mathrm{G}$ respectively of Eqs . 12 and 13 and q is the appropriate m om entum.

Solution of this equation gives $\mathrm{E}=2 \mathrm{~K}(1 \quad \mathrm{cosq})$. For a band ofm read-1 sites (from a to $a+m$ 1) surrounded by 0 s on both sides, use of $\mathrm{Eqs}$. . 12 , 13, and 16 gives 6 equations di erent from Eq. 23 for the sites a 1; $a ; a+1 ; a+m \quad 1 ; a+m ; a+m+1$. In order of these sites, they are

$$
\begin{aligned}
& \text { (aAB) } \quad\left(\mathrm{aC}_{1} \mathrm{D}_{1}\right)=0 \\
& \left(\mathrm{aC}_{1} \mathrm{D}_{1}\right)(\mathbb{E} \quad 2 \mathrm{~K})+\mathrm{K}\left(\begin{array}{ll}
(\mathrm{a} & 1 \mathrm{AB})+\mathrm{K} \quad\left(\mathrm{a}+1 \mathrm{C}_{2} \mathrm{D}_{2}\right)=0
\end{array}\right. \\
& \left(\mathrm{a}+1 \mathrm{C}_{2} \mathrm{D}_{2}\right)(\mathrm{E} \quad 2 \mathrm{~K})+\mathrm{K} \quad\left(\mathrm{aC}_{1} \mathrm{D}_{1}\right)+\mathrm{K} \quad\left(\mathrm{a}+2 \mathrm{C}_{2} \mathrm{D}_{2}\right)=0 \\
& \left(\mathrm{a}+\mathrm{m} \quad 1 \mathrm{C}_{2} \mathrm{D}_{2}\right)(\mathbb{E} \quad 2 \mathrm{~K})+\mathrm{K} \quad\left(\mathrm{a}+\mathrm{m} \quad 2 \mathrm{C}_{2} \mathrm{D}_{2}\right)+\mathrm{K} \quad\left(\mathrm{a}+\mathrm{m} \mathrm{C}_{3} \mathrm{D}_{3}\right)=0 \\
& \left(a+\mathrm{mC}_{3} \mathrm{D}_{3}\right)(\mathrm{E} \quad 2 \mathrm{~K})+\mathrm{K} \quad\left(\mathrm{a}+\mathrm{m} \quad 1 \mathrm{C}_{2} \mathrm{D}_{2}\right)+\mathrm{K}(\mathrm{a}+\mathrm{m}+1 \mathrm{FG})=0 \\
& (a+m F G) \quad\left(a+m C_{3} D_{3}\right)=0:
\end{aligned}
$$

Here Eq. 23 has been used to simplify the rst and last equations to rem ove (a 1AB) (E $2 \mathrm{~K})$ and ( $a+m+1 \mathrm{~F}$ ) (E 2 K$)$.

The rst equation is used to rem ove ( $\mathrm{aC}_{1} \mathrm{D}_{1}$ ) from the next two equations. C om bination of the resulting two equations with Eq. 23 gives a 22 m atrix connecting ( $\mathrm{a}+1 \mathrm{C}_{2} \mathrm{D}_{2}$ ) to (aA B ). In a sim ilar way the second 3 equations are used to give a $2 \quad 2 \mathrm{~m}$ atrix connecting $(a+m F G)$ to $\left(a+m \quad 1 C_{2} D_{2}\right)$. The product (taken in the correct order) of these two $m$ atrioes and $a \operatorname{m}$ atrix connecting $\left(a+m \quad 1 C_{2} D_{2}\right)$ to $\left(a+1 C_{2} D_{2}\right)$ gives the nal result. $T$ he $m$ atrix for $W_{m}$ is obtained by setting $a=1$ and translating the result by another $m+1$ potential free sites.

## REFERENCES

[1] D. Shechtm an, I. B lech, D . G ratias, and J. C ahn, P hys. R ev. Letters 531951 (1984).
[2] T.Fu j̈wara and T.O gawa (Eds) Q uasicrystals, P roceedings of the 112th Taniguchi Sym posium, Shim a, M ie P refecture, Japan N ov 14-19 1989, Springer Series in Solid State Sciences 93, Springer Verlag N ew York.
[3] D. . I iV incenzo and P. Steinhardt E ds., Q uasicrystals the State of the A rt, in D irections in C ondensed M atter P hysics Vol. 11, W orld Scienti c Singapore 1991.
[4] A. B ovier and J-M . G hez, J. Phys. A : M ath. Gen. 282313 (1995).
[5] Let A be a nite alphabet, A the set of all nite words of A, and $A^{N}$ the set of all one way in nite words ofA. A substitution rule replaces each letter ofA with a word from A. For each a sequence of words in A can be generated by starting w ith and iterating the substitution rule. The lim it sequence in $A^{N}$ is a substitution sequence if it is invariant under the substitution.
[6] J M . Luck, Phys. Rev. B 39 5834, (1989)
[7] J. Bellissard, A . B ovier, and J-M . G hez, C om m un. M ath. Phys. 135379 (1991)
[8] A. Sutø, Jour Stat. P hys. 56525 (1989).
[9] A. B ovier and J-M . G hez, C om m un. M ath. Phys. 15845 (1993); 166431 (1994).
[10] M . H omquist and M . Johansson, J. P hys. A M ath. Gen. 28479 (1995).
[11] C.S.Ryu, In m ook K im , G.Y.Oh, and M.H.Lee, Phys. Rev.B 4914991 (1994).
[12] Y . A vishai, D. Berend, and D. G laubm an, Phys. Rev. Lett. 721842 (1994).
[13] Y . A vishai and D . Berend, P hys. Rev B-II 436873 (1994).
[14] Y.A vishaiand D.Berend, Phys. Rev B-II 452717 (1992).
[15] V .M . G asparian and A. Gh. K hachatrian, Solid State C om m un. 851061 (1993).
[16] P. E rdos and R . C . Hemdon, Solid State C om m un. 98495 (1996).
[17] R . Landauer, P hil. M ag. 21 863, (1970).
[18] P.E rdos and R.C.H emdon, Adv.Phys, 31 65, (1982)
[19] C. R oy and A.Khan, Phys. Rev. B , 4914979 (1994):
[20] C . R oy and A . K han, Solid State C om m un. 92241 (1994).
[21] C. R oy and C.Basu, Phys. Stat. Sol (b) 177315 (1993).
[22] P. Benio, To A ppear in Phys Rev. Letters
[23] R . Landauer, Philos. Trans. R oy. Soc. London A 353367 91995); P hysics Letters A 217 188 (1996); Physics Today $44 \mathrm{No.5}$,23 (1991).
[24] A. Peres, P hys. Rev. A 323266 (1985)
[25] W . H. Zurek, Phys. Rev. Lett. 53391 (1984)
[26] P. Benio , Jour. Stat. P hys. 22563 (1980); A nn. NY A cad. Sci. 480475 (1986).
[27]P. Benio , Phys.Rev A 541106 (1996).
[28] D . D eutsch, P roc. R oy. Soc. London Ser. A 40097 (1985); 42573 (1989).
[29] S. Lloyd, Sci. Am erican 273 No.4, 140, (1995); Joumal of M odem Optics, 412503 (1994).
[30] D.P.D iV incenzo, Science, 270255 (1995)
[31] I.L.Chuang, R.La am me, P IN . Shor, and W .H. Zurek, Science 2701633 (1995)
[32]W . G.Unnuh, Phys, Rev.A 51992 (1995).
[33] R . La am m e, C.M iguel, J. Pablo Paz, and W . H. Zurek, P hys Rev. Letters bf 77198 (1996).
[34] R . Feynm an, Int Jour. T heoret. Phys. 21467 (1982).
[35] S. Lloyd, Science 2731073 (1996); C. Zalka E cient Sim ulation of Q uantum Sysytem s by Q uantum Computers, Report No. BUTP-96/11, M arch 25, 1996, Los A lam os A rchives quant-ph/9603026.
[36] P. Shor, in P roceedings of the 35th A nnualSym posium on the Foundations of C om puter Science ( $\mathbb{E E E}$ C om puter Society, Los A lam itos, CA 1994), p.124. For a recent review see A. E kert and R. Jozsa, Rev. M od. Phys. 68733 (1996).
[37] P. W . Shor, Phys. Rev.A 52 R 2493 (1990); R.LaF lam me, C. M iquel, J. P. Paz, and W . H. Zurek, Phys. Rev. Letters 77198 (1996).
[38] S. Lloyd, Phys. Rev. Letters, bf 75346 (1995); D. P. D iVencenzo, Phys. Rev. A 51 1015 (1995); D .D eutsch, A. B arenco, and A.E kert, P roc. R oy. Soc. London A 449669 (1995).
[39] This sequence rst appeared in the literature in conjunction with work on relaxation of hierarchical system s (B.A.H uberm an and M.K erzberg, J. P hys. A : M ath. G en. 18 L331 (1985)) and recently in work on aperiodic Ising chains ( $F$. Igloi and L. Turban, Los A lam osA rchives cond-m at/9606118). The sequence is referred to as the hierarchical sequence. The author thanks D r. Turban for these references.
[40] R . Feynm an, O ptics N ew s, 1111 (1985); reprinted in Foundations of Physics, 16507 (1986).
[41] P. R . H alm os, A H ibert Space P roblem Book, 2nd Edition, Springer Verlag, N ew Y ork, 1982.
[42] M . K olar am d F.N ori, Phys. Rev. B 421062 (1990)
[43] M. Q ue elec, Substitution D ynam icalSystem $s$-SpectralA nalysis, Lecture $N$ otes in $M$ athem atics 1294, Editors A. D old and B . E ckm ann, Springer V erlag, B erlin 1987.
[44] D.P.D iV ioenzo and P. J. Steinhardt, P rogress and C urrent Issues in Q uasicrystals, in D .P.D iV incenzo and P . J. Steinhardt Eds., Q uasicrystals the State of the A rtD irections in C ondensed M atter P hysics-Vol. 11, W orld Scienti c Singapore 1991, pp 1-15.
[45] For exam ple: M . K ohm oto, L. P. K adano , and C. Tang, Phys. R ev. Letters 501870 (1983); M . K ohm oto, Intemational Jour. M odem P hys. 131 (1987); G . G um bs and M . K.A li, Phys. Rev. Letters 601081 (1988); M . K olar and M.K.A li, Phys. Rev B 39 426 (1989).

## FIGURECAPTIONS

Figure 1. In itial and $F$ inalStates for $C$ ounting $G Q T M$ for the $F$ irst $2^{n} B$ inary $N$ um bers. A $1 l$ lattioe qubits are in state j0i except those at sites 0 and $n+1$ whidn are in state $2 i$. $T$ he in itialand nalhead states are show $n$ as $w$ ave packets $w$ ith intemal head states j $j 0 i$ and jli to the left and right respectively.

Figure 2. The Potential Distribution for $N=6$. The potential height, in units of K (1 ) , is plotted against path position. A potential height of 1 or 2 corresponds respectively to one or both term $s$ of Eq. 11 being active.

Figure 3. Energy B and Spectra for the A ssociated P eriodic System s for $=0: 999$ for three values of $N$ as a Function of $M$ om entum $k$. The $m$ om entum range is from the least value forwhich $\jmath^{\top} r Z_{N} j^{\prime} 2$ up to $k=$ arcoss. W thin each long band or ribbon associated w ith each $N$, the upper horizontal line segm ents correspond to energy bands; the lower horizontal segm ents correspond to energy gaps. Very short bands or gaps appear as points. For $N=15$ and especially $N=18$, band and gap density is too high in severalm om entum regions to be resolved at the scale show $n$.

Figure 4. Energy B and Spectra for the A ssociated Periodic System for the Sam e Values of $N$ as were used in $F$ igure 3 but w ith $=0: 99$. See the caption of $F$ igure 3 for additional details. N ote that, com pared to the spectra in $F$ igure 3, the gaps are $m$ uch w ider and the energy bands are narrow er.

Figure 5. Energy B and Spectra for the A ssociated Periodic System for $=0: 9$ and $\mathrm{N}=6 ; 8 ; 10$. The caption of F igure 3 gives $m$ ore details. Lower values of N are show n because at the higher values of $N$ the uctuations of $T r Z_{N}$ are so extrem e that calculations becom e im practical. Even for the values of $N=8$ and $N=10$ there are no assurances that the grid used (w th m ore than 7,000 equally spaced points) is ne enough to capture all bands.

Figure 6. The Log (base 10) of the Landauer Resistance P lotted as a Function of the $M$ om entum for $N=10$ and $=0: 999$. The $m$ om entum range is the same as that used in Figure 3. T he corresponding energy band spectrum for the associated periodic system, from Figure 4, is shown at the bottom of the gure.

Figure 7. An Expanded P lot of the Log (base 10) of the Landauer R esistance as a Function of k for $\mathrm{N}=10$ and $=0: 999$ over the R ange $0: 034 \mathrm{k} \quad 0: 040$. The corresponding expanded band spectrum is also show $n$. T he correspondence betw een $m$ inim a in log LR and band-gap boundaries is clearly shown as is the decrease in the magnitude of the $m$ inim a w ith increasing gap w idth.

Figure 8. The Log (base 10) of the Landauer Resistance as a Function of the $M$ om entum for $\mathrm{N}=18$ and $=0: 999$. The corresponding energy band spectnum is also shown. In order to show values of $\log \mathrm{L} R$ in the neighborhood of 0 , the ordinate values were cut o at
20. F luctuations in $\log \mathrm{LR}$ are so rapid and extrem e that individual $m$ axim a and $m$ in $m$ a in the neighborhood of 0 are not resolved.

Figure 9. Expanded $P$ lot of the Log (base 10) of the Landauer Resistance for $N=18$, $=0: 999$ over the range 0:032 $\mathrm{k} \quad 0: 033 \mathrm{~T}$ he corresponding expanded band spectrum is also shown. The range is a sm all region in F igure 8 show ing especially rapid uctuations. The correlation between the height of maxim a in $\log L R$ and widths of associated gaps is shown clearly.

Figure 10. A Very H igh Resolution $P$ lot of the Log (base 10) of the Landauer Resistance for $N=18$, $=0: 999$ O ver a Very Sm all M om entum Region of 0:03225 k 0:03228. T he expanded band spectrum is also shown. Individual m axim a and m inim a are clearly resolved. A s is the case in $F$ igure 7 for $N=10$, the location ofm inim a at or near band-gap boundaries, and the decrease in the $m$ inim a w ith increasing gap widths are clearly show $n$.

Figure 11. The Log (base 10) of the Landauer R esistance P lotted as a Function of the M om entum for $\mathrm{N}=10$ and $=0: 99$. The corresponding band spectrum is also show n . The m om entum range is from the least value ofk for which $\mathfrak{J r} r Z_{\mathrm{N}} \mathrm{j}^{\prime} 2$ up to arcoos. . High $m$ axim a in log LR are clearly assocated w ith w ide gaps.

Figure 12. P lot of the Log (base 10) of the Landauer R esistance and C orresponding B and Spectrum for $\mathrm{N}=8$ and $=0: 9$. The values of k range from the m allest value for which打 $r \mathrm{Z}_{\mathrm{N}} \mathrm{j}^{\prime} 2$ to arcoos. The values of $\log \mathrm{LR}$ are cuto at 20 in order to show the ne structure at sm aller values.

Figure 13. Expanded $P$ lot of the Log (base 10) of the Landauer Resistance and C orresponding $B$ and Spectrum for $N=8$ and $=0: 9$ for $0: 400 \mathrm{k} \quad 0: 415$. The association between $m$ in m a in log LR and band-gap boundaries is weaker than for values of closer to 1 in that som em inim a are close to the $m$ iddle of gaps.

$n+1$













